Oxford Instruments - Atomic Layer Deposition (ALD) System – OpAL
THICKNESS CONTROL AT THE ATOMIC SCALE

• Wafer: Up to 200mm wafers & pieces directly on stage
• Bubbled Liquid and Solid Precursors: Up to 3
• Max Precursor Source Temperature: 200°C (Jacket)
• Thermal Gas Precursors = 2 internally
  • Plasma Gases = Up to 8 in externally mounted gas pod
• Wafer Stage Temperature Range: 25°C - 400°C
• Current precursor available: Al₂O₃